



74LVC1G17

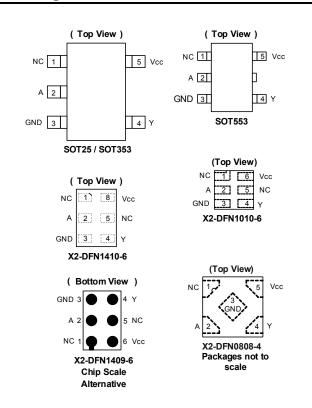
### SINGLE SCHMITT-TRIGGER BUFFER

### Description

The 74LVC1G17 is a single 1-input Schmitt-trigger buffer with a standard push-pull output. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

Y = A

### **Pin Assignments**



### Features

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- Wide Supply Voltage Range from 1.65V to 5.5V
- ±24mA Output Drive at 3.3V
- CMOS Low Power Consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs Accept up to 5.5V
- ESD Protection Tested per JESD 22
   Exceeds 2000-V Human Body Model (A114))

  Exceeds 1000-V Charged Device Model (C101)
  - Latch-Up Exceeds 100mA per JESD 78, Class I
- Range of Package Options
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

 An Automotive-Compliant Part is Available Under Separate Datasheet (<u>74LVC1G17Q</u>)

### Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- Wide Array of Products such as:
  - PCs, Networking, Notebooks, Netbooks,
  - Computer Peripherals, Hard Drives, CD/DVD ROM
  - TV, DVD, DVR, Set Top Box
  - Cell Phones, Personal Navigation / GPS
  - MP3 Players, Cameras, Video Recorders

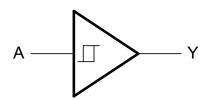
- Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



# **Pin Descriptions**

Pin Name	Description
А	Data Input
GND	Ground
Y	Data Output
V <sub>CC</sub>	Supply Voltage

Logic Diagram



# **Function Table**

Input	Output
Α	Y
н	Н
L	L

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage Applied to Output in High Impedance or IOFF State	-0.5 to 6.5	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input Clamp Current VI < 0	-50	mA
I <sub>OK</sub>	Output Clamp Current	-50	mA
lo	Continuous Output Current	±50	mA
I <sub>CC</sub> , I <sub>GND</sub>	Continuous Current through V <sub>CC</sub> or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Abaoluto Movimum Potingo

4. Stresses beyond the absolute maximum can result in immediate failure or reduced reliability. These are stress values and device Notes: operation should be within recommend values.

5. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.



# Recommended Operating Conditions (Note 6)

Symbol		Parameter	Min	Max	Unit		
		Operating	1.65	5.5	V		
Vcc	Operating Voltage	Data retention only	1.5	_	V		
VI	Input Voltage		0	5.5	V		
Vo	Output Voltage		0	V <sub>CC</sub>	V		
		V <sub>CC</sub> = 1.65V	_	-4			
		$V_{CC} = 2.3V$	_	-8			
		V <sub>CC</sub> = 2.7V	_	-12			
lон	High-Level Output current		_	-16	mA		
		$V_{CC} = 3V$	_	-24			
		$V_{CC} = 4.5V$	_	-32			
		V <sub>CC</sub> = 1.65V	_	4			
		$V_{CC} = 2.3 V$	_	8			
		V <sub>CC</sub> = 2.7V	_	12			
IOL	Low-Level Output current		_	16	mA		
		$V_{CC} = 3V$	_	24			
		V <sub>CC</sub> = 4.5V	_	32	1		
TA	Operating Free-Air Temperature	_	-40	+125	°C		

Note: 6. Unused inputs should be held at  $V_{CC}$  or Ground.



Symbol	Parameter	Test Conditions	V <sub>CC</sub>	Min	Тур	Мах	Unit
		_	1.65V	0.70	_	1.20	_
		_	2.3V	1.11	_	1.60	_
V <sub>T</sub> +	Positive-Going Input Threshold Voltage	_	3V	1.50	_	2.00	_
	Threshold voltage	_	4.5V	2.16	_	2.74	_
			5.5V	2.61		3.33	_
			1.65V	0.30		0.72	_
			2.3V	0.58		1.00	_
V <sub>T-</sub>	Negative-Going Input Threshold Voltage		3V	0.80		1.30	_
	Threshold voltage		4.5V	1.21		1.95	_
			5.5V	1.45		2.35	_
			1.65V	0.30		0.62	_
			2.3V	0.40		0.80	_
$\Delta V_{T}$	Hysteresis (V <sub>T+</sub> - V <sub>T-</sub> )		3V	0.35		1.00	_
		-	4.5V	0.55	_	1.10	_
		-	5.5V	0.60	_	1.20	_
		Ι <sub>ΟΗ</sub> = -100μΑ	1.65V to 5.5V	V <sub>CC</sub> – 0.1		_	
		I <sub>OH</sub> = -4mA	1.65V	1.2	_	_	
		I <sub>OH</sub> = -8mA	2.3V	1.9	_	_	
Voh	High Level Output Voltage	I <sub>OH</sub> = -12mA	2.7V	2.2	_		V
		I <sub>OH</sub> = -16mA	- 3∨	2.4	_		
		I <sub>OH</sub> = -24mA	30	2.3	_	_	
		I <sub>OH</sub> = -32mA	4.5V	3.8	_		
		I <sub>OL</sub> = 100μΑ	1.65V to 5.5V	—	_	0.1	
		I <sub>OL</sub> = 4mA	1.65V	—	_	0.45	
		I <sub>OL</sub> = 8mA	2.3V	—	_	0.3	
V <sub>OL</sub>	Low-Level Output Voltage	I <sub>OL</sub> = 12mA	2.7V	—	_	0.4	V
		I <sub>OL</sub> = 16mA	- 3∨	_	_	0.4	
		I <sub>OL</sub> = 24mA	30	—	_	0.55	
		I <sub>OL</sub> = 32mA	4.5V	_	_	0.55	
lı –	Input Current	V <sub>I</sub> = 5.5V or GND	0 to 5.5V	—	-	± 5	μA
IOFF	Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O}$ = 5.5V	0	_		± 10	μA
Icc	Supply Current	V <sub>I</sub> = 5.5V of GND I <sub>O</sub> = 0	1.65V to 5.5V	_	_	10	μA
Δlcc	Additional Supply Current	Input at V <sub>CC</sub> – 0.6V	3V to 5.5V	_	_	500	μA

# **Electrical Characteristics** (@ T<sub>A</sub> = -40°C to +85°C. All typical values are at V<sub>CC</sub> = 3.3V, T<sub>A</sub> = +25°C.)



Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit	
		_	1.65V	0.70	_	1.20	_	
		_	2.3V	1.11	_	1.60		
V <sub>T+</sub>	Positive-Going Input	_	3V	1.50	_	2.00		
	Threshold Voltage	_	4.5V	2.16	_	2.74		
		_	5.5V	2.61	_	3.33		
		_	1.65V	0.30	_	0.75	_	
		_	2.3V	0.58	_	1.03	_	
V <sub>T-</sub>	Negative-Going Input	_	3V	0.80	_	1.33	_	
	Threshold Voltage	_	4.5V	1.21	_	1.95	_	
		_	5.5V	1.45	_	2.35	_	
		_	1.65V	0.30	_	0.62	_	
		_	2.3V	0.37	_	0.80	_	
$\Delta V_{T}$	Hysteresis (V <sub>T+</sub> - V <sub>T-</sub> )	_	3V	0.32	_	1.00	_	
	(V +- V -)	_	4.5V	0.50	_	1.20	_	
		_	5.5V	0.55	_	1.40	_	
		Ι <sub>ΟΗ</sub> = -100μΑ	1.65V to 5.5V	$V_{CC} - 0.1$				
		I <sub>OH</sub> = -4mA	1.65V	0.95	_	_	—	
		I <sub>OH</sub> = -8mA	2.3V	1.7	_	—		
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -12mA	2.7V	1.9	_	_	V	
		I <sub>OH</sub> = -16mA	2)/	2.2	_	_		
		I <sub>OH</sub> = -24mA	3V	2.0	_	_		
		I <sub>OH</sub> = -32mA	4.5V	3.4	_	—		
		I <sub>OL</sub> = 100μΑ	1.65V to 5.5V	_	_	0.1		
		I <sub>OL</sub> = 4mA	1.65V	_	_	0.7		
		I <sub>OL</sub> = 8mA	2.3V	_	_	0.45		
V <sub>OL</sub>	Low-Level Output Voltage	I <sub>OL</sub> = 12mA	2.7V	—	_	0.6	V	
		I <sub>OL</sub> = 16mA	2)/	_	_	0.6		
		I <sub>OL</sub> = 24mA	- 3V	_	_	0.8		
		I <sub>OL</sub> = 32mA	4.5V	_	_	0.8		
l <sub>l</sub>	Input Current	$V_1 = 5.5V$ or GND	0 to 5.5V	_	_	±5	μA	
IOFF	Power Down Leakage Current	$V_{\rm I}$ or $V_{\rm O}$ = 5.5V	0	_	_	±10	μA	
Icc	Supply Current	V <sub>I</sub> = 5.5V of GND I <sub>O</sub> = 0	1.65V to 5.5V	_	_	10	μA	
ΔIcc	Additional Supply Current	Input at V <sub>CC</sub> – 0.6V	3V to 5.5V	_	_	500	μA	

# **Electrical Characteristics** (continued) (@ T<sub>A</sub> = -40°C to +125°C. All typical values are at V<sub>CC</sub> = 3.3V, T<sub>A</sub> = +25°C.)



Symbol	Parameter	Test Conditions	Vcc	Min	Тур	Max	Unit
		SOT25		—	204	—	
		SOT353		—	371	—	
	SOT553		—	231	—		
$\theta_{JA}$	Thermal Resistance	X2-DFN0808-4	(Note 7)	—	400	—	°C/W
Junction-to-Ambient	X2-DFN1010-6		—	445	—		
		X2-DFN1409-6		—	470	—	-
		X2-DFN1410-6		—	460	—	
		SOT25		—	52	—	
		SOT353		—	143	—	
		SOT553		—	105	—	
θ <sub>JC</sub>	Thermal Resistance	X2-DFN0808-4	(Note 7)	—	225	—	°C/W
	Junction-to-Case	X2-DFN1010-6		_	250	_	-
		X2-DFN1409-6		_	275	_	
	-	X2-DFN1410-6		_	265		

### Package Characteristics (All typical values are at V<sub>CC</sub> = 3.3V, T<sub>A</sub> = +25°C.)

Note: 7. Test condition for each of the 7 package types: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

# **Switching Characteristics**

$T_A = -40^{\circ}C$ to $+85^{\circ}C$	, C <sub>L</sub> = 15pF	as noted	(See Figure	1)
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Parameter	From	To Output	V <sub>CC</sub> = ± 0.7			= 2.5V ).2V		= 3.3V ).3V	V <sub>CC</sub> ±0	= 5V .5V	Unit
	Input		Min	Мах	Min	Мах	Min	Мах	Min	Max	
t <sub>PD</sub>	A	Y	1.0	9.9	0.7	5.5	0.7	4.6	0.7	4.4	ns

 $T_A$  = -40°C to +85°C, C<sub>L</sub> = 30pF or 50pF as noted (See Figure 2)

Parameter	Parameter From	То	V <sub>CC</sub> = 1.8V ± 0.15V		V <sub>CC</sub> = 2.5V ± 0.2V		V <sub>CC</sub> = 3.3V ± 0.3V		V <sub>CC</sub> = 5V ± 0.5V		Unit
	Input	Output	Min	Max	Min	Max	Min	Мах	Min	Max	
t <sub>PD</sub>	А	Y	1.0	11	0.7	6.5	0.7	5.5	0.7	5	ns

 $T_A$  = -40°C to +125°C,  $C_L$  = 15pF as noted (See Figure 1)

Parameter From	То		V <sub>CC</sub> = 1.8V ± 0.15V		V <sub>CC</sub> = 2.5V ± 0.2V		V <sub>CC</sub> = 3.3V ± 0.3V		<sub>c</sub> = 5V 0.5V	Unit	
	Input Output	Output	Min	Мах	Min	Max	Min	Мах	Min	Max	
t <sub>PD</sub>	А	Y	1.0	12.5	0.7	7.5	0.7	6.5	0.7	5.5	ns

 $T_A$  = -40°C to +125°C,  $C_L$  = 30pF or 50pF as noted (See Figure 2)

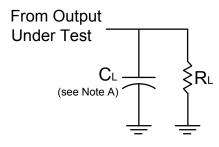
Parameter	From To Input Output		V <sub>CC</sub> = ± 0.			= 2.5V 0.2V	V <sub>CC</sub> = ± 0		V <sub>CC</sub> ±0	= 5V .5V	Unit
		Min	Мах	Min	Max	Min	Max	Min	Max		
t <sub>PD</sub>	А	Y	1.0	14.0	0.7	8.5	0.7	7.0	0.7	6.5	ns



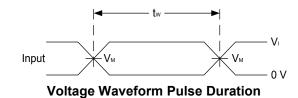
# **Operating Characteristics**

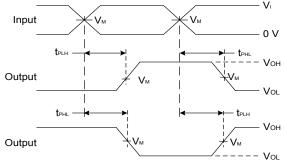
$T_A = +25^{\circ}C$							
	Demonster	Test	V <sub>CC</sub> = 1.8V	V <sub>CC</sub> = 2.5V	V <sub>CC</sub> = 3.3V	V <sub>CC</sub> = 5V	Unit
	Parameter	Conditions	Тур	Тур	Тур	Тур	Unit
CPD	Power Dissipation Capacitance	f = 10MHz	20	22	23	25	pF

### **Parameter Measurement Information**



N/	In	puts	V	0	
Vcc	VI	t <sub>R</sub> /t <sub>F</sub>		CL	RL
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1ΜΩ
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1ΜΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1ΜΩ
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	15pF	1ΜΩ





**Voltage Waveform Propagation Delay Times** Inverting and Non Inverting Outputs

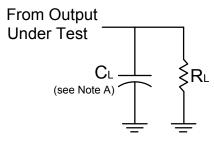
#### Figure 1. Load Circuit and Voltage Waveforms

Notes:

- A. Includes test lead and test apparatus capacitance. B. All pulses are supplied at pulse repetition rate  $\leq$  10MHz. C. Inputs are measured separately one transition per measurement. D. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>PD</sub>.



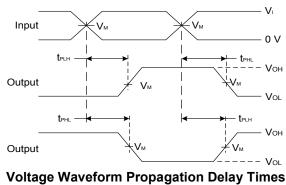
# Parameter Measurement Information (continued)



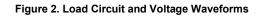
Vee	Inj	outs	Ver	C	D.	
V <sub>cc</sub>	VI	t <sub>R</sub> /t <sub>F</sub>	V <sub>M</sub>	CL	RL	
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1kΩ	
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	500Ω	
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω	
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω	



**Voltage Waveform Pulse Duration** 



Inverting and Non Inverting Outputs

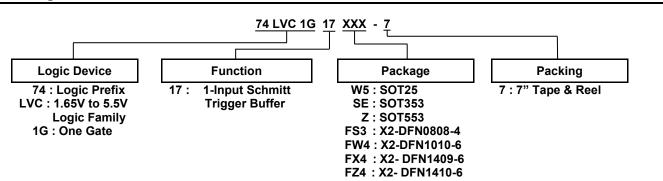


Notes:

- A. Includes test lead and test apparatus capacitance. B. All pulses are supplied at pulse repetition rate  $\leq$  10MHz. C. Inputs are measured separately one transition per measurement. D. t<sub>PLH</sub> and t<sub>PHL</sub> are the same as t<sub>PD</sub>.



### Ordering Information (Note 8)



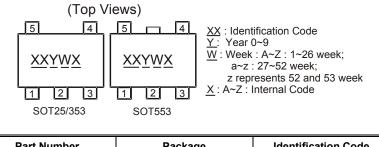
Davias	Baakawa Cada	Package	7" Tape and Reel	
Device	Package Code	(Notes 9, 10)	Quantity	Part Number Suffix
74LVC1G17W5-7	W5	SOT25	3,000/Tape & Reel	-7
74LVC1G17SE-7	SE	SOT353	3,000/Tape & Reel	-7
74LVC1G17Z-7	Z	SOT553	4,000/Tape & Reel	-7
74LVC1G17FS3-7	FS3	X2-DFN0808-4	5,000/Tape & Reel	-7
74LVC1G17FW4-7	FW4	X2-DFN1010-6	5,000/Tape & Reel	-7
74LVC1G17FX4-7	FX4	X2-DFN1409-6 (Chip Scale Alternative)	5,000/Tape & Reel	-7
74LVC1G17FZ4-7	FZ4	X2-DFN1410-6	5,000/Tape & Reel	-7

 For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
 Pad layout as shown in Diodes Incorporated's package outline PDFs, which can be found on our website at http://www.diodes.com/package-outlines.html. 10. The taping orientation is located on our website at https://www.diodes.com/assets/Packaging-Support-Docs/ap02007.pdf.

Notes:



### (1) SOT25, SOT353 and SOT553



Part Number	Package	Identification Code
74LVC1G17W5-7	SOT25	UR
74LVC1G17SE-7	SOT353	UR
74LVC1G17Z-7	SOT553	UR

#### (2) DFN Packages



 $\begin{array}{l} \underbrace{XX} : \text{Identification Code} \\ \underline{Y} : \text{Year } 0~9 \\ \underline{W} : \text{Week : } A~Z : 1~26 \text{ week;} \\ a~z : 27~52 \text{ week;} \\ z \text{ represents } 52 \text{ and } 53 \text{ week} \\ \underline{X} : A~Z : \text{Internal Code} \end{array}$ 

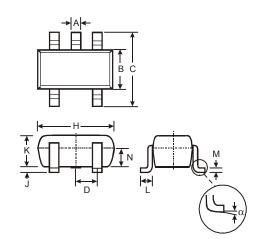
Part Number	Package	Identification Code
74LVC1G17FS3-7	X2-DFN0808-4	WR
74LVC1G17FW4-7	X2-DFN1010-6	UR
74LVC1G17FX4-7	X2-DFN1409-6	MH
74LVC1G17FZ4-7	X2-DFN1410-6	UR



# **Package Outline Dimensions**

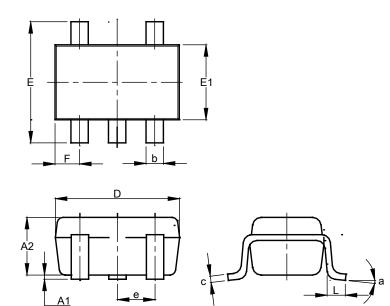
Please see http://www.diodes.com/package-outlines.html for the latest version.

### (1) Package Type: SOT25



	SOT25					
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D	-	1	0.95			
н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
κ	1.00	1.30	1.10			
L	0.35	0.55	0.40			
М	0.10	0.20	0.15			
Ν	0.70	0.80	0.75			
α	0°	8°	-			
All D	imensi	ons in	mm			

### (2) Package Type: SOT353



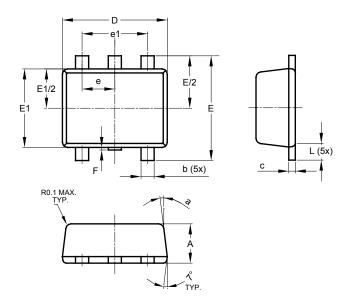
	SOT353					
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
С	0.10	0.22	0.11			
D	1.80	2.20	2.15			
ш	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	C	).650 B	SC			
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All	Dimen	sions	in mm			



# Package Outline Dimensions (continued)

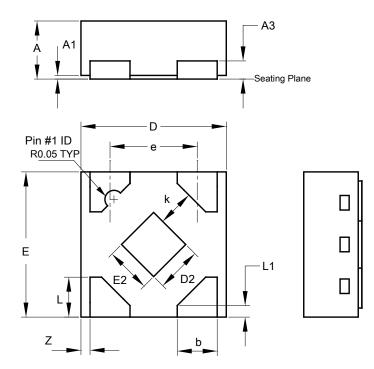
Please see http://www.diodes.com/package-outlines.html for the latest version.

(3) Package Type: SOT553



	0.01		
	SOT		_
Dim	Min	Max	Тур
Α	0.55	0.62	0.60
b	0.15	0.30	0.20
С	0.10	0.18	0.15
D	1.50	1.70	1.60
Е	1.55	1.70	1.60
E1	1.10	1.25	1.20
е	0.	50 BS(	0
e1	1.	00 BS(	0
F	0.00	0.10	
L	0.10	0.30	0.20
а	6°	8°	7°
	Dimens	ions ir	n mm

### (4) Package Type: X2-DFN0808-4



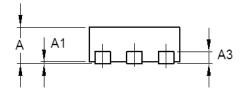
	X2-DFN0808-4					
Dim	Min	Мах	Тур			
Α	0.25	0.35	0.30			
A1	0	0.04	0.02			
A3	-	-	0.13			
b	0.17	0.27	0.22			
D	0.75	0.85	0.80			
D2	0.15	0.35	0.25			
E	0.75	0.85	0.80			
E2	0.15	0.35	0.25			
е	-	-	0.48			
k	0.20	-	-			
L	0.17	0.27	0.22			
L1	0.02	0.12	0.07			
z	-	-	0.05			
A	II Dimens	sions in I	mm			

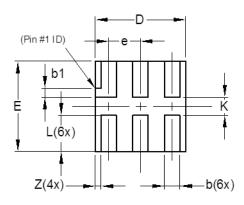


# Package Outline Dimensions (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

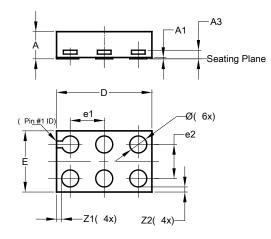
#### (5) Package Type: X2-DFN1010-6





	X2-DFN1010-6					
Dim	Min	Max	Тур			
Α	—	0.40	0.39			
A1	0.00	0.05	0.02			
A3	_		0.13			
b	0.14	0.20	0.17			
b1	0.05	0.15	0.10			
D	0.95	1.05	1.00			
E	0.95	1.05	1.00			
е	_	_	0.35			
L	0.35	0.45	0.40			
K	0.15	_	_			
Z	—	_	0.065			
A	II Dimensi	ions in m	n			

### (6) Package Type: X2-DFN1409-6



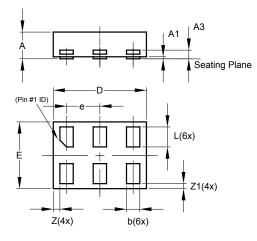
	X2-DFN1409-6					
Dim	Min	Max	Тур			
Α	-	0.40	0.39			
A1	0	0.05	0.02			
A3	-	-	0.13			
Ø	0.20	0.30	0.25			
D	1.35	1.45	1.40			
E	0.85	0.95	0.90			
e1	-	-	0.50			
e2	-	-	0.50			
Z1	-	-	0.075			
Z2	-	-	0.075			
All [	Dimen	sions iı	n mm			



# Package Outline Dimensions (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(7) Package Type: X2-DFN1410-6



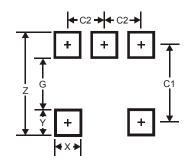
	X2-DFN1410-6		
Dim	Min	Max	Тур
Α		0.40	0.39
A1	0.00	0.05	0.02
A3			0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
E	0.95	1.05	1.00
е			0.50
L	0.25	0.35	0.30
Z		_	0.10
Z1	0.045	0.105	0.075
All Dimensions in mm			



# **Suggested Pad Layout**

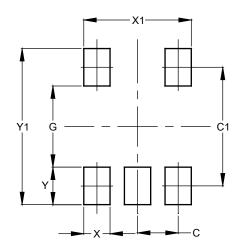
Please see http://www.diodes.com/package-outlines.html for the latest version.

(1) Package Type: SOT25



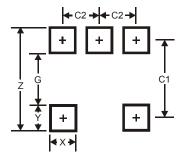
Dimensions	Value
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

### (2) Package Type: SOT353



Dimensions	Value (in mm)
С	0.650
C1	1.900
G	1.300
Х	0.420
X1	1.720
Y	0.600
Y1	2.500

(3) Package Type: SOT553



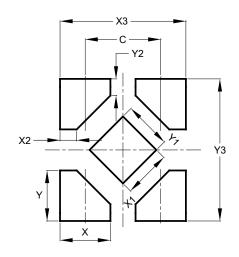
Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



# Suggested Pad Layout (continued)

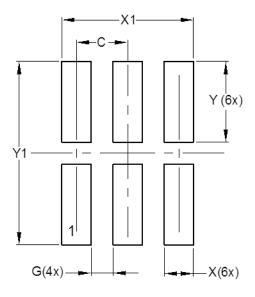
Please see http://www.diodes.com/package-outlines.html for the latest version.

(4) Package Type: X2-DFN0808-4

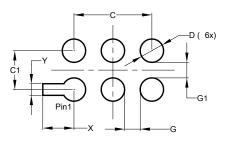


Dimensions	Value
С	0.480
Х	0.320
X1	0.300
X2	0.106
X3	0.800
Y	0.320
Y1	0.300
Y2	0.106
Y3	0.900

### (5) Package Type: X2-DFN1010-6



### (6) Package Type: X2-DFN1409-6



Dimensions	Value (in mm)
С	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

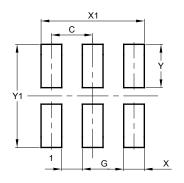
Dimensions	Value (in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
Х	0.400
Y	0.150



### Suggested Pad Layout (continued)

Please see http://www.diodes.com/package-outlines.html for the latest version.

(7) Package Type: X2-DFN1410-6



Dimensions	Value	
	(in mm)	
С	0.500	
G	0.250	
Х	0.250	
X1	1.250	
Y	0.525	
Y1	1.250	

### **Mechanical Data**

#### SOT25

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Mate Tin Plated Leads, Solderable per MIL-STD-202, Method 208 🐵
- Weight: 0.016 grams (Approximate)

#### SOT353

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Mate Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)

#### SOT553

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Mate Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.003 grams (Approximate)

#### X2-DFN0808-4

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208 @
- Weight: 0.001 grams (Approximate)

#### X2-DFN1010-6

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208 @
- Weight: 0.001 grams (Approximate)

#### X2-DFN1409-6

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208 @
- Weight: 0.002 grams (Approximate)

### X2-DFN1410-6

- Moisture Sensitivity: Level 1 per J-STD-020
- 🛛 Terminals: Finish NiPdAu Nickel Palladium Gold, Solderable per MIL-STD-202, Method 208 函
- Weight: 0.002 grams (Approximate)



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